

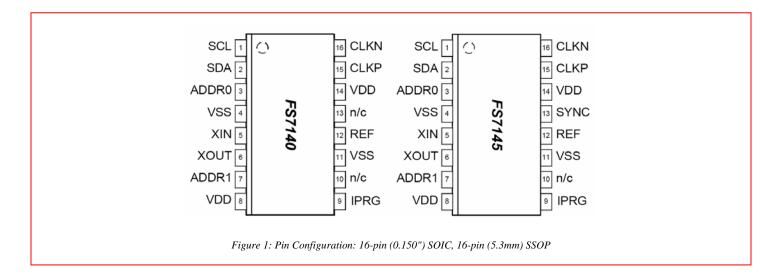
1.0 Key Features

- · Extremely flexible and low-jitter phase locked loop (PLL) frequency synthesis
- No external loop filter components needed
- 150MHz CMOS or 340MHz PECL outputs
- Completely configurable via l²C[™]-bus
- Up to four FS714x can be used on a single I²C-bus
- 3.3V operation
- · Independent on-chip crystal oscillator and external reference input
- · Very low "cumulative" jitter

2.0 Description

The FS714x (FS7140x or FS7145x) is a monolithic CMOS clock generator/regenerator IC designed to minimize cost and component count in a variety of electronic systems. Via the I²C-bus interface, the FS714x can be adapted to many clock generation requirements.

The length of the reference and feedback dividers, their fine granularity and the flexibility of the post divider make the FS714x the most flexible stand-alone PLL clock generator available.



3.0 Applications

- Precision frequency synthesis
- Low-frequency clock multiplication
- Video line-locked clock generation
- Laser beam printers (FS7145)

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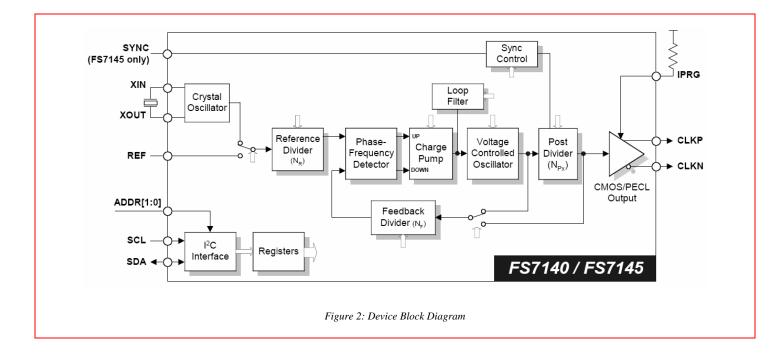


Table	1: FS714	0 Pin Descrip	otions
Pin	Туре	Name	Description
1	DI	SCL	Serial interface clock (requires an external pull-up)
2	DIO	SDA	Serial interface data input/output (requires an external pull-up)
3	DI_{D}	ADDR0	Address select bit "0"
4	Р	VSS	Ground
5	AI	XIN	Crystal oscillator feedback
6	AO	XOUT	Crystal oscillator drive
7	DI_{D}	ADDR1	Address select bit "1"
8	Р	VDD	Power supply (+3.3V nominal)
9	AI	IPRG	PECL current drive programming
10	-	n/c	No connection
11	Р	VSS	Ground
12	DI	REF	Reference frequency input
13	-	n/c	No connection
14	Р	VDD	Power supply (+3.3V nominal)
15	DO	CLKP	Clock output
16	DO	CLKN	Inverted clock output
Kev A	I Analog I	nnut $\Delta O = \Delta na$	log Output: DI = Digital Input: DI ^U = Input with Internal Pull-up: DI ₂ = Input with Intern

Key: Al: Analog Input; AO = Analog Output; DI = Digital Input; DI^U = Input with Internal Pull-up; DI_D = Input with Internal Pull-down; DIO = Digital Input/Output; DI-3 = Three-Level Digital Input; DO = Digital Output; P = Power/Ground; # = Active Low Pin

Table	Table 2: FS7145 Pin Descriptions						
Pin	Туре	Name	Description				
1	DI	SCL	Serial interface clock (requires an external pull-up)				
2	DIO	SDA	Serial interface data input/output (requires an external pull-up)				
3	DI_{D}	ADDR0	Address select bit "0"				
4	Р	VSS	Ground				
5	AI	XIN	Crystal oscillator feedback				
6	AO	XOUT	Crystal oscillator drive				
7	DI_{D}	ADDR1	Address select bit "1"				
8	Р	VDD	Power supply (+3.3V nominal)				
9	AI	IPRG	PECL current drive programming				
10	-	n/c	No connection				
11	Р	VSS	Ground				
12	DI	REF	Reference frequency input				
13	DI ^U	SYNC	Synchronization input				
14	Р	VDD	Power supply (+3.3V nominal)				
15	DO	CLKP	Clock output				
16	DO	CLKN	Inverted clock output				

Key: Al: Analog Input; AO = Analog Output; DI = Digital Input; DI^U = Input with Internal Pull-up; DI_D = Input with Internal Pull-down; DIO = Digital Input/Output; DI-3 = Three-Level Digital Input; DO = Digital Output; P = Power/Ground; # = Active Low Pin

4.0 Functional Block Diagram

4.1 Phase Locked Loop (PLL)

The PLL is a standard phase- and frequency-locked loop architecture. The PLL consists of a reference divider, a phase-frequency detector (PFD), a charge pump, an internal loop filter, a voltage-controlled oscillator (VCO), a feedback divider, and a post divider.

The reference frequency (generated by either the on-board crystal oscillator or an external frequency source), is first reduced by the reference divider. The integer value that the frequency is divided by is called the modulus and is denoted as NR for the reference divider. This divided reference is then fed into the PFD.

The VCO frequency is fed back to the PFD through the feedback divider (the modulus is denoted by NF).

The PFD will drive the VCO up or down in frequency until the divided reference frequency and the divided VCO frequency appearing at the inputs of the PFD are equal. The input/output relationship between the reference frequency and the VCO frequency is then:

$$\frac{f_{VCO}}{N_F} = \frac{f_{REF}}{N_R}$$

This basic PLL equation can be rewritten as

$$f_{VCO} = f_{REF} \left(\frac{N_{|F|}}{N_{R}} \right)$$

A post divider (actually a series combination of three post dividers) follows the PLL and the final equation for device output frequency is:

$$f_{CLK} = f_{REF} \left(\frac{N_F}{N_R} \right) \left(\frac{1}{N_{Px}} \right)$$

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4.1.1. Reference Divider

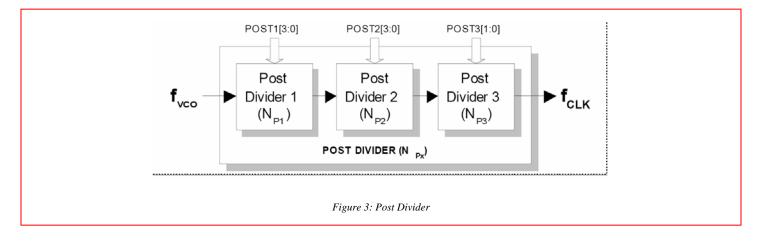
The reference divider is designed for low phase jitter. The divider accepts the output of either the crystal oscillator circuit or an external reference frequency. The reference divider is a 12 bit divider, and can be programmed for any modulus from 1 to 4095 (divide by 1 not available on date codes prior to 0108).

4.1.2. Feedback Divider

The feedback divider is based on a dual-modulus divider (also called dual-modulus prescaler) technique. It permits division by any integer value between 12 and 16383. Simply program the FBKDIV register with the binary equivalent of the desired modulus. Selected moduli below 12 are also permitted. Moduli of: 4, 5, 8, 9, and 10 are also allowed (4 and 5 are not available on date codes prior to 0108).

4.1.3. Post Divider

The post divider consists of three individually programmable dividers, as shown in Figure 3.



The moduli of the individual dividers are denoted as NP1, NP2 and NP3, and together they make up the array modulus NPX.

$N_{PX} = N_{P1} \times N_{P2} \times N_{P3}$

The post divider performs several useful functions. First, it allows the VCO to be operated in a narrower range of speeds compared to the variety of output clock speeds that the device is required to generate. Second, the extra integer in the denominator permits more flexibility in the programming of the loop for many applications where frequencies must be achieved exactly.

Note that a nominal 50/50 duty factor is always preserved (even for selections which have an odd modulus).

See Table 8 for additional information.

4.1.4. Crystal Oscillator

The FS7140 is equipped with a Pierce-type crystal oscillator. The crystal is operated in parallel resonant mode. Internal load capacitance is provided for the crystal. While a recommended load capacitance for the crystal is specified, crystals for other standard load capacitances may be used if great precision of the reference frequency (100ppm or less) is not required.

4.1.5. Reference Divider Source MUX

The source of frequency for the reference divider can be chosen to be the device crystal oscillator or the REF pin by the REFDSRC bit.

When not using the crystal oscillator, it is preferred to connect XIN to VSS. Do not connect to XOUT.

When not using the REF input, it is preferred to leave it floating or connected to V_{DD} .

4.1.6. Feedback Divider Source MUX

The source of frequency for the feedback divider may be selected to be either the output of the post divider or the output of the VCO by the FBKDSRC bit.

Ordinarily, for frequency synthesis, the output of the VCO is used. Use the output of the post divider only where a deterministic phase relationship between the output clock and reference clock are desired (line-locked mode, for example).

4.1.7. Device Shutdown

Two bits are provided to effect shutdown of the device if desired, when it is not active. SHUT1 disables most externally observable device functions. SHUT2 reduces device quiescent current to absolute minimum values. Normally, both bits should be set or cleared together.

Serial communications capability is not disabled by either SHUT1 or SHUT2.

4.2 Differential Output Stage

The differential output stage supports both CMOS and pseudo-ECL (PECL) signals. The desired output interface is chosen via the programming registers.

If a PECL interface is used, the transmission line is usually terminated using a Thévenin termination. The output stage can only sink current in the PECL mode, and the amount of sink current is set by a programming resistor on the LOCK/IPRG pin. The ratio of output sink current to IPRG current is 13:1. Source current for the CLKx pins is provided by the pull-up resistors that are part of the Thévenin termination.

4.2.1. Example

Assume that it is desired to connect a PECL-type fanout buffer right next to the FS7140.

Further assume:

- V_{DD} = 3.3V
- Desired V_{HI} = 2.4V
- Desired V_{LO} = 1.6V
- Equivalent R_{LOAD} = 75 ohms

Then:

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 \begin{array}{l} \textit{R1 (from CLKP and CLKN output to VDD) =} \\ & \textit{R}_{LOAD} * \textit{V}_{DD} / \textit{V}_{HI} = \\ & 75 * 3.3 / 2.4 = \\ & 103 \textit{ ohms} \end{array} \\ \hline \textit{R2 (from CLKP and CLKN output to GND) =} \\ & \textit{R}_{LOAD} * \textit{V}_{DD} / (\textit{V}_{DD} - \textit{V}_{HI}) = \\ & 75 * 3.3 / (3.3 - 2.4) = \\ & 275 \textit{ ohms} \end{array} \\ \hline \textit{Rprgm (from VDD to IPRG pin) =} \\ & 26 * (\textit{V}_{DD} * \textit{R}_{LOAD}) / (\textit{V}_{HI} - \textit{V}_{LO}) / 3 = \\ & 2.68 \textit{ Kohms} \end{array}
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4.3 SYNC Circuitry

The FS7145 supports nearly instantaneous adjustment of the output CLK phase by the SYNC input. Either edge direction of SYNC (positive-going or negative-going) is supported.

Example (positive-going SYNC selected): Upon the negative edge of SYNC input, a sequence begins to stop the CLK output. Upon the positive edge, CLK resumes operation, synchronized to the phase of the SYNC input (plus a deterministic delay). This is performed by control of the device post-divider. Phase resolution equal to ½ of the VCO period can be achieved (approximately down to 2ns).

5.0 I²C-bus Control Interface

This device is a read/write slave device meeting all Philips I²C-bus specifications except a "general call." The bus has to be controlled by a master device that generates the serial clock SCL, controls bus access and generates the START and STOP conditions while the device works as a slave. Both master and slave can operate as a transmitter or receiver, but the master device determines which mode is activated. A device that sends data onto the bus is defined as the transmitter, and a device receiving data as the receiver.

 I^{2} C-bus logic levels noted herein are based on a percentage of the power supply (V_{DD}). A logic-one corresponds to a nominal voltage of V_{DD}, while a logic-zero corresponds to ground (V_{SS}).

5.1 Bus Conditions

Data transfer on the bus can only be initiated when the bus is not busy. During the data transfer, the data line (SDA) must remain stable whenever the clock line (SCL) is high. Changes in the data line while the clock line is high will be interpreted by the device as a START or STOP condition. The following bus conditions are defined by the l^2 C-bus protocol.

5.1.1. Not Busy

Both the data (SDA) and clock (SCL) lines remain high to indicate the bus is not busy.

5.1.2. START Data Transfer

A high to low transition of the SDA line while the SCL input is high indicates a START condition. All commands to the device must be preceded by a START condition.

5.1.3. STOP Data Transfer

A low to high transition of the SDA line while SCL input is high indicates a STOP condition. All commands to the device must be followed by a STOP condition.

5.1.4. Data Valid

The state of the SDA line represents valid data if the SDA line is stable for the duration of the high period of the SCL line after a START condition occurs. The data on the SDA line must be changed only during the low period of the SCL signal. There is one clock pulse per data bit.

Each data transfer is initiated by a START condition and terminated with a STOP condition. The number of data bytes transferred between START and STOP conditions is determined by the master device, and can continue indefinitely. However, data that is overwritten to the device after the first eight bytes will overflow into the first register, then the second, and so on, in a first-in, first-overwritten fashion.

5.1.5. Acknowledge

When addressed, the receiving device is required to generate an acknowledge after each byte is received. The master device must generate an extra clock pulse to coincide with the acknowledge bit. The acknowledging device must pull the SDA line low during the high period of the master acknowledge clock pulse. Setup and hold times must be taken into account.

The master must signal an end of data to the slave by not generating and acknowledge bit on the last byte that has been read (clocked) out of the slave. In this case, the slave must leave the SDA line high to enable the master to generate a STOP condition.

5.2 I²C-bus Operation

All programmable registers can be accessed randomly or sequentially via this bi-directional two wire digital interface. The crystal oscillator does not have to run for communication to occur.

The device accepts the following I^2C -bus commands:

5.2.1. Slave Address

After generating a START condition, the bus master broadcasts a seven-bit slave address followed by a R/W bit. The address of the device is:

A6	A5	A4	A3	A2	A1	A0
1	0	1	1	0	Х	Х

where X is controlled by the logic level at the ADDR pins. The selectable ADDR bits allow four different FS7140 devices to exist on the same bus. Note that every device on an I^2 C-bus must have a unique address to avoid possible bus conflicts.

5.2.2. Random Register Write Procedure

Random write operations allow the master to directly write to any register. To initiate a write procedure, the R/W bit that is transmitted after the seven-bit device address is a logic-low. This indicates to the addressed slave device that a register address will follow after the slave device acknowledges its device address. The register address is written into the slave's address pointer. Following an acknowledge by the slave, the master is allowed to write eight bits of data into the addressed register. A final acknowledge is returned by the device, and the master generates a STOP condition.

If either a STOP or a repeated START condition occurs during a register write, the data that has been transferred is ignored.

5.2.3. Random Register Read Procedure

Random read operations allow the master to directly read from any register. To perform a read procedure, the R/W bit that is transmitted after the seven-bit address is a logic-low, as in the register write procedure. This indicates to the addressed slave device that a register address will follow after the slave device acknowledges its device address. The register address is then written into the slave's address pointer.

Following an acknowledge by the slave, the master generates a repeated START condition. The repeated START terminates the write procedure, but not until after the slave's address pointer is set. The slave address is then resent, with the R/W bit set this time to a logic-high, indicating to the slave that data will be read. The slave will acknowledge the device address, and then transmits the eight-bit word. The master does not acknowledge the transfer but does generate a STOP condition.

5.2.4. Sequential Register Write Procedure

Sequential write operations allow the master to write to each register in order. The register pointer is automatically incremented after each write. This procedure is more efficient than the random register write if several registers must be written.

To initiate a write procedure, the R/W bit that is transmitted after the seven-bit device address is a logic-low. This indicates to the addressed slave device that a register address will follow after the slave device acknowledges its device address. The register address is written into the slave's address pointer. Following an acknowledge by the slave, the master is allowed to write up to eight bytes of data into the addressed register before the register address pointer overflows back to the beginning address.

An acknowledge by the device between each byte of data must occur before the next data byte is sent.

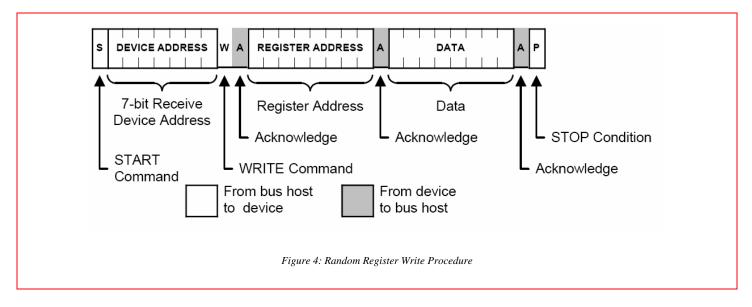
Registers are updated every time the device sends an acknowledge to the host. The register update does not wait for the STOP condition to occur. Registers are therefore updated at different times during a sequential register write.

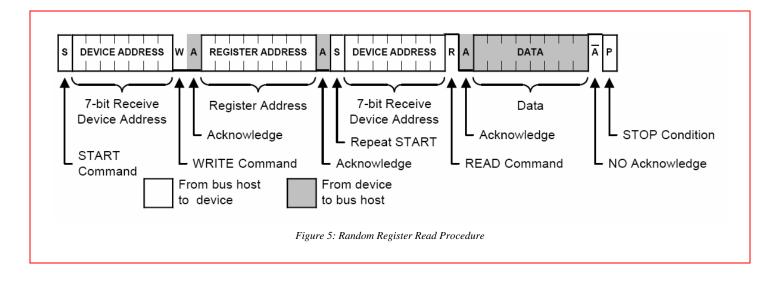
5.2.5. Sequential Register Read Procedure

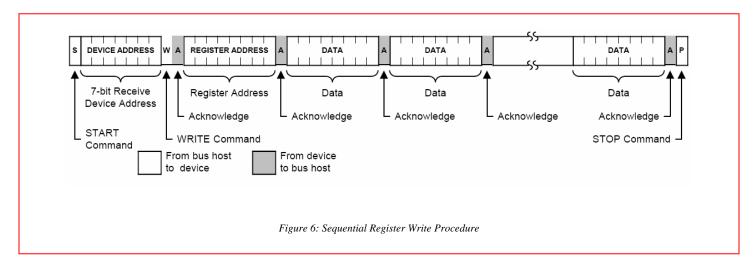
Sequential read operations allow the master to read from each register in order. The register pointer is automatically incremented by one after each read. This procedure is more efficient than the random register read if several registers must be read.

To perform a read procedure, the R/W bit that is transmitted after the seven-bit address is a logic-low, as in the register write procedure. This indicates to the addressed slave device that a register address will follow after the slave device acknowledges its device address. The register address is then written into the slave's address pointer.

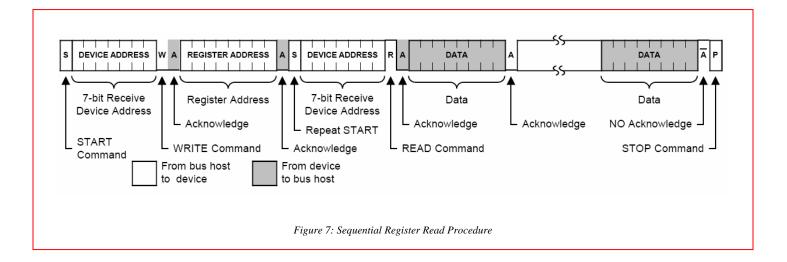
Following an acknowledge by the slave, the master generates a repeated START condition. The repeated START terminates the write procedure, but not until after the slave's address pointer is set. The slave address is then resent, with the R/W bit set this time to a logic-high, indicating to the slave that data will be read. The slave will acknowledge the device address, and then transmits all eight bytes of data starting with the initial addressed register. The register address pointer will overflow if the initial register address is larger than zero. After the last byte of data, the master does not acknowledge the transfer but does generate a STOP condition.







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6.0 Programming Information

All register bits are cleared to zero on power-up. All register bits may be read back as written.

Table 3: FS	S7140 Register M	lap						
Address	BIT 7	BIT 6	BIT 5	BIT 4	BIT 3	BIT 2	BIT 1	BIT 0
Byte 7	Reserved (Bit 63) Must be set to "0"	Reserved (Bit 62) Must be set to "0"	(Bit 61) Must be set to "0"	Reserved (Bit 60) Must be set to "0"	Reserved (Bit 59) Must be set to "0"	Reserved (Bit 58) Must be set to "0"	Reserved (Bit 57) Must be set to "0"	Reserved (Bit 56) Must be set to "0"
Byte 6	Reserved (Bit 55) Must be set to "0"	Reserved (Bit 54) Must be set to "0"	SHUT2 (Bit 53) 0 = Normal 1 = Powered down	Reserved (Bit 52) Must be set to "0"	Reserved (Bit 51) Must be set to "0"	Reserved (Bit 50) Must be set to "0"	Reserved (Bit 49) Must be set to "0"	Reserved (Bit 48) Must be set to "0"
Byte 5	Reserved (Bit 47) Must be set to "0"	LC (Bit 46) Loop filter cap select	LR[1] (Bit 45) Loop filter res	LR[0] (Bit 44) sistor select	Reserved (Bit 43) Must be set to "0"	Reserved (Bit 42) Must be set to "0"	CP[1] (Bit 41) Charge pump	CP[0] (Bit 40) o current select
Byte 4	CMOS (Bit 39) 0 = PECL 1 = CMOS	FBKDSRC (Bit 38) 0 = VCO output 1 = Post divider output	FBKDIV[13] (Bit 37) <i>8192</i>	FBKDIV[12] (Bit 36) 4096	FBKDIV[11] (Bit 35) 2048	FBKDIV[10] (Bit 34) 1024	FBKDIV[9] (Bit 33) 512	FBKDIV[8] (Bit 32) 256
				Se	e Section 4.1.2 for disal	lowed FBKDIV values		
Byte 3	FBKDIV[7] (Bit 31) 128	FBKDIV[6] (Bit 30) 64	FBKDIV[5] (Bit 29) 32	FBKDIV[4] (Bit 28) 16	FBKDIV[3] (Bit 27) 8	FBKDIV[2] (Bit 26) 4	FBKDIV[1] (Bit 25) 2	FBKDIV[0] (Bit 24) 1
			Si	ee Section 4.1.2 for disa	llowed FBKDIV values			
Byte 2	POST2[3] (Bit 23)	POST2[2] (Bit 22)	POST2[1] (Bit 21)	POST2[0] (Bit 20)	POST1[3] (Bit 19)	POST1[2] (Bit 18)	POST1[1] (Bit 17)	POST1[0] (Bit 16)
		s = N + 1 (N = 0 to 11); S					= N +1 (N = 0 to 11); Se	
Byte 1	POST3[1] (Bit 15) Modulus = 1,2,4,	POST3[0] (Bit 14) or 8; See Table 8	SHUT1 (Bit 13) 0 = Normal 1 = Powered down	REFDSRC (Bit 12) 0 = Crystal oscillator 1 = REF pin	REFDIV[11] (Bit 11) 2048	REFDIV[10] (Bit 10) 1024	REFDIV[9] (Bit 9) 512	REFDIV[8] (Bit 8) 256
Byte 0	REFDIV[7] (Bit 7) 128	REFDIV[6] (Bit 6) 64	REFDIV[5] (Bit 5) 32	REFDIV[4] (Bit 4) 16	REFDIV[3] (Bit 3) 8	REFDIV[2] (Bit 2) 4	REFDIV[1] (Bit 1) 2	REFDIV[0] (Bit 0) 1

Table 4: FS	S7145 Register M	lap						
Address	BIT 7	BIT 6	BIT 5	BIT 4	BIT 3	BIT 2	BIT 1	BIT 0
Byte 7	Reserved (Bit 63) Must be set to "0"	Reserved (Bit 62) Must be set to "0"	Reserved (Bit 61) Must be set to "0"	Reserved (Bit 60) Must be set to "0"	Reserved (Bit 59) Must be set to "0"	Reserved (Bit 58) Must be set to "0"	Reserved (Bit 57) Must be set to "0"	Reserved (Bit 56) Must be set to "0"
Byte 6	Reserved (Bit 55) Must be set to "0"	Reserved (Bit 54) Must be set to "0"	SHUT2 (Bit 53) 0 = Normal 1 = Powered down	Reserved (Bit 52) Must be set to "0"	Reserved (Bit 51) Must be set to "0"	Reserved (Bit 50) Must be set to "0"	SYNCPOL (Bit 49) "0" = negative "1" = positive	(Bit 48) "0" = negative "1" = positive
Byte 5	Reserved (Bit 47) Must be set to "0"	LC (Bit 46) Loop filter cap select	LR[1] (Bit 45) Loop filter re	LR[0] (Bit 44) esistor select	Reserved (Bit 43) Must be set to "0"	Reserved (Bit 42) Must be set to "0"	CP[1] (Bit 41) Charge pump	CP[0] (Bit 40)
Byte 4	CMOS (Bit 39) 0 = PECL 1 = CMOS	FBKDSRC (Bit 38) 0 = VCO output 1 = Post divider output	FBKDIV[13] (Bit 37) 8192	FBKDIV[12] (Bit 36) 4096	FBKDIV[11] (Bit 35) 2048	FBKDIV[10] (Bit 34) 1024	FBKDIV[9] (Bit 33) 512	FBKDIV[8] (Bit 32) 256
					See Section 4.1.2 for disa	llowed FBKDIV values		
Byte 3	FBKDIV[7] (Bit 31) 128	FBKDIV[6] (Bit 30) 64	FBKDIV[5] (Bit 29) 32	FBKDIV[4] (Bit 28) 16	FBKDIV[3] (Bit 27) 8 isallowed FBKDIV values	FBKDIV[2] (Bit 26) 4	FBKDIV[1] (Bit 25) 2	FBKDIV[0] (Bit 24) 1
	POST2[3]	POST2[2]	POST2[1]	POST2[0]	POST1[3]	POST1[2]	POST1[1]	POST1[0]
Byte 2	(Bit 23)	(Bit 22) = N +1 (N = 0 to 11); Set	(Bit 21)	(Bit 20)	(Bit 19)	(Bit 18)	(Bit 17) = N +1 (N = 0 to 11); Se	(Bit 16)
	POST3[1]	POST3[0]	SHUT1	REFDSRC	REFDIV[11]	REFDIV[10]	REFDIV[9]	REFDIV[8]
Byte 1	(Bit 15)	(Bit 14) or 8; See Table 8	(Bit 13) 0 = Normal 1 = Powered down	(Bit 12) 0 = Crystal oscillator 1 = REF pin	(Bit 11) 2048	(Bit 10) 1024	(Bit 9) 512	(Bit 8) 256
Byte 0	REFDIV[7] (Bit 7) 128	REFDIV[6] (Bit 6) 64	REFDIV[5] (Bit 5) 32	REFDIV[4] (Bit 4) 16	REFDIV[3] (Bit 3) 8	REFDIV[2] (Bit 2) 4	REFDIV[1] (Bit 1) 2	REFDIV[0] (Bit 0) 1

Table 5: Device	Table 5: Device Configuration Bits							
Name	Description							
REFDSRC	Reference divider source [0] = crystal oscillator / [1] = REF pin							
FBKDSRC	Feedback divider source [0] = VCO output / [1] = post divider output							
SHUT1	Shutdown1 [0] = normal / [1] = powered down							
SHUT2	Shutdown2 [0] = normal / [1] = powered down							
CMOS	CLKP/CLKN output mode [0] = PECL output / [1] CMOS output							

Table 6: Main Loop Tuning Bits

	Loop Turning Dits	
Name	Description	
	Charge pump current	
	[00]	2.0µA
CP[1:0]	[01]	4.5µA
	[10]	11.0µA
	[11]	22.5µA
	Loop filter resistor select	
	[00]	400ΚΩ
LR[1:0]	[01]	133ΚΩ
	[10]	30KΩ
	[11]	12ΚΩ
	Loop filter capacitor select	
LC	[0]	185pF
	[1]	500pF

Table 7: PLL Divider Control Bits

Name	Description
REFDIV[11:0]	Reference divider (N _R)
FBKDIV[13:0]	Feedback divider (N _R)

Table 8: SYNC Control Bits (FS7145 only)

Name	Description
SYNCEN	Sync enable
	[0] = disabled / [1] = enabled
SYNCPOL	Sync polarity
	[0] = negative edge / [1] = positive edge

Table 9: Post Div	ider Control Bits	
Name	Description	
	Post divider #1 (N _{P1}) modulus	
	[0000]	1
	[0001]	2
	[0010]	3
	[0011]	4
	[0100]	5
	[0101]	6
	[0110]	7
POST1[3:0]	[0111]	8
	[1000]	9
	[1001]	10
	[1010]	11
	[1011]	12
	[1100]	
	[1101]	Do not use
	[1110]	Do not use
	[1111]	
	Post divider #2 (N _{P2}) modulus	
	[0000]	1
	[0001]	2
	[0010]	3
	[0011]	4
	[0100]	5
	[0101]	6
	[0110]	7
POST2[3:0]	[0111]	8
	[1000]	9
	[1001]	10
	[1010]	11
	[1011]	12
	[1100]	
	[1101]	Do not use
	[1110]	Do not use
	[1111]	
	Post divider #3 (N _{P3}) modulus	
	[00]	1
POST3[1:0]	[01]	2
	[10]	4
	[11]	8

7.0 Electrical Specifications

Table 10: Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Units
Supply voltage, dc (V _{SS} = ground)	V _{DD}	$V_{SS} - 0.5$	4.5	V
Input voltage, dc	V ₁	$V_{SS} - 0.5$	V _{DD} + 0.5	V
Output voltage, dc	Vo	$V_{SS} - 0.5$	V _{DD} + 0.5	V
Input clamp current, dc ($V_1 < 0$ or $V_1 > V_{DD}$)	I _{IK}	-50	50	mA
Output clamp current, dc ($V_1 < 0$ or $V_1 > V_{DD}$)	Ι _{οκ}	-50	50	mA
Storage temperature range (non-condensing)	Ts	-65	150	°C
Ambient temperature range, under bias	TA	-55	125	°C
Junction temperature	TJ		150	°C
Re-flow solder profile				Per IPC/JEDEC J-STD-020B
Input static discharge voltage protection (MIL-STD 883E, Method 3015.7)			2	kV

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. These conditions represent a stress rating only and functional operation of the device at these or any other conditions above the operational limited noted in this specification is not implied. Exposure to maximum rating conditions for extended conditions may affect device performance, functionality and reliability.



CAUTION: ELECTROSTATIC SENSITIVE DEVICE

Permanent damage resulting in a loss of functionality or performance may occur if this device is subjected to a high-energy electrostatic discharge.

Table 11: Operating Conditions

Parameter	Symbol	Conditions/Description	Min.	Тур.	Max.	Units
Supply voltage	V _{DD}		3.0	3.3	3.6	V
Ambient operating temperature range	T _A		0		70	°C

Table 12: DC Electrical Specifications

OverallCMOS mode; $F_{XTAL} = 15MHz; F_{VC0} =$ Supply current, dynamic I_{DD} CMOS mode; $F_{XTAL} = 15MHz; F_{VC0} =$ 35mASupply current, static I_{DDL} SHUT1, SHUT2 bit both "1"400700 μ ASerial Communication I/O (SDA, SCL)High-level input voltageV.H.0.8"V_{DD}VHigh-level input voltageV.H.0.8"V_{DD}VVLow-level input voltageV.H.0.33"V_{DD}VInput leakage currentI,SDA, SCL in read condition-10+10 μ AAddress Select Input (ADDR0, ADDR1)ILSDA in acknowledge condition; $V_{SDA} = 0.4V$ 514mAHigh-level input voltageV.H.V_{DD} - 1.0VVLow-level input voltageV.H.V_{DD} - 1.0VVLow-level input current (pull-down)I.H.V_{ADDRx} = V_{DD}0.8VHigh-level input currentI.H.V_{ADDRx} = V_{DD}-11 μ AReference Frequency Input (REF)V-11 μ ALow-level input currentI.H.V_{REF} = V_{DD}-11 μ ALow-level input voltageV.H.V_{DD} - 1.0VLow-level input voltageV.H30WHigh-level input currentI.H.Low-level input currentI.H.V_{REF} = V_{DD}-11 μ ALow-level input voltageV.H30VWHigh-level input currentI.H.V_{RE	Parameter	Symbol	Conditions/Description	Min.	Тур.	Max.	Units
Supply current, dynamicIoo400MHz; Fack = 200MLz; does not include load current35mASupply current, staticIooSHUT1, SHUT2 bit both *1"400700µAStrial Communication IV (GSA, SCL)Ve0.8"Vac0.8"Vac0.2"VacVeHigh-level input voltageVe0.8"Vac0.2"Vac0.2"VacVeHystersis voltageVe0.8"Vac0.3"Vac0.2"VacVeLow-level put voltageVeSDA, SCL in read condition; VacoA = 0.4V514mAAddress Sciect Input (ADDRO, ADDR)VeVac0.8"Vac0.8"VacVacLow-level input voltageVeVac0.8"VacVacVacVacLow-level input voltageVeVac0.8VVacVacVacVacLow-level input voltageVeVac0.8VVacVacVacVacVacHigh-level input voltageVeVac0.8VVac<	Overall						
Serial Communication VO (SDA, SCL)VHigh-level input voltageV0.8"V0.2"VWigh-level input voltageV0.33"V0.2"VHystersis voltageV0.3"V0.2"VLow-level input toxingeV0.3"V0.2"VLow-level output sink current (SDA)ISDA in acknowledge condition; V0.4"V5Address Select Input (ADRA ADDR)VN0.40.8"VHigh-level input voltageVV0.8"V0.8"VLow-level output voltageV0.8"V0.8"VVHigh-level input voltageV0.8"V0.8"VVHigh-level input current (pull-down)IVV0.8"VVHigh-level input current (pull-down)IVV0.8"VVHigh-level input voltageVV11µAReference Frequency Input (REF)V0.8"VVVHigh-level input current (pull-down)IVV-11New elevel input current (pull-down)IVV-30µALow-level input current (pull-down)IVV-30µALow-level input voltageVV-11µALow-level input voltageVV-11µALow-level input voltageV-11µALow-level input voltageV-11µALow-level input voltageV-11µALow-le	Supply current, dynamic	I _{DD}	400MHz; F_{CLK} = 200MHz; does not include		35		mA
High-level input voltageVal. $0.8^{+}V_{DO}$ VUndervel input voltageVal. $0.33^{+}V_{DO}$ VHysteresis voltageVal. $0.33^{+}V_{DO}$ VInput leakage currentI.SDA, SCL in read condition; Vaga = 0.4V514mAAddress Select input (ADDRO, ADDR)Val.SDA in acknowledge condition; Vaga = 0.4V514mAAddress Select input (ValDRO, ADDR)Val.Val.Val.Val.Val.Val.Val.Igh-level input voltageVal.Va	Supply current, static	I _{DDL}	SHUT1, SHUT2 bit both "1"		400	700	μA
Low-level input voltage VL 0.2 VD00 V 0.2 VD00 V 0.3 VD00 V 0.5 A 0.4 V 5 14 M M Address Select Input (ADR0, ADDR1) V 0.4 V 0.5 A 0.4 V 5 14 M Address Select Input voltage VL VL V000 V 0.0 V	Serial Communication I/O (SDA, SCL)						
Hysteresis voltageVmgs0.33°V_{DD}VInput leakage currentInSDA, SCL in read condition-10+10µALow-level output sink current (SDA)IouSDA, SCL in read condition; V_{SDA} = 0.4V514mAAddress Select Input voltageVmVpo - 1.0VVLow-level input voltageVm0.88VIngh-level input current (pull-down)ImV_ADDRx = Vpo30µALow-level input currentImV_ADDRx = 0V-11µAReference Frequency Input (REF)Vin0.88VVLow-level input voltageVinVac0.88VHigh-level input voltageVinVm = 00.88VLow-level input voltageVinVm = 0-30µASyme Control Input CurrentImVm = 0-30µASyme Control Input CurrentImVm = 0-30µALow-level input voltageVm-0.88VVLow-level input current (pull-down)ImVm = 0-30µALow-level input currentImVm = 0-30µALow-level input currentImVm = 0-30µALow-level input currentImVm = 0-40µALow-level input currentImVm = 0-8.5mALow-level input currentImVm = 0-1010Low-level input currentImVm = 0-3010Control Current <td></td> <td>VIH</td> <td></td> <td>0.8*V_{DD}</td> <td></td> <td></td> <td>V</td>		VIH		0.8*V _{DD}			V
Input leakage current I, I, SDA, SCL in read condition -10 +10 μ A Address Sclect Input (ADDR0, ADDR1) High-level input voltage V,		VIL				0.2*V _{DD}	V
Low-level output sink current (SDA) Address Select Input (ADDR0, ADDR1)DASDA in acknowledge condition; $V_{BDA} = 0.4V$ 514mAHigh-level input voltageV _H $V_{0D} - 1.0$ VLow-level input current (pull-down)I _H $V_{ADDR*} = V_{DD}$ 30 μ ALow-level input current (pull-down)I _H $V_{ADDR*} = V_{DD}$ 30 μ ALow-level input current (pull-down)I _H $V_{ADDR*} = 0V$ -11 μ AReference Frequency Input (REF)-0.8VHigh-level input current (pull-down)I _H $V_{REF} = V_{DD}$ -11 μ ALow-level input current (pull-down)I _H $V_{REF} = V_{DD}$ -11 μ ALow-level input current (pull-down)I _H $V_{REF} = V_{DD}$ -11 μ ALow-level input current (pull-down)I _H $V_{REF} = V_{DD}$ -11 μ ALow-level input current (pull-down)I _H $V_{REF} = V_{DD}$ -11 μ ALow-level input current (pull-down)I _H $V_{REF} = V_{DD}$ -11 μ ALow-level input current (pull-down)I _H $V_{REF} = 0V$ -30 μ ALow-level input current (pull-down)I _H $V_{REF} = 0V$ -30 μ ALow-level input current (pull-down)I _H $V_{REF} = 0V$ -30 μ ALow-level input current (pull-down)I _H $V_{REF} = 0V$ -30 μ ALow-level input currentI _H $V_{REF} = 0V$ -30 μ A <td>Hysteresis voltage</td> <td>V_{hys}</td> <td></td> <td></td> <td>0.33*V_{DD}</td> <td></td> <td>V</td>	Hysteresis voltage	V _{hys}			0.33*V _{DD}		V
Address Select Input (ADDR0, ADDR1)High-level input voltageV _H V _{DD} - 1.0VHigh-level input voltageV _H 0.8VHigh-level input current (pull-down)I _H V _{ADDRx} = V _{DD} 30µAReference Frequency Input (REF)V _{ADDRx} = 0V-11µAReference Frequency Input (REF)V _H V _{DD} - 1.0VVHigh-level input voltageV _H 0.8VVHigh-level input currentI _H V _{REF} = V _{DD} -11µASyne Control Input (GPNC)V _{REF} = 0V-30µAVSyne Control Input (GYNC)V _{REF} = 0V-30VVHigh-level input voltageV _H V _{REF} = V _{DD} -11µASyne Control Input (GYNC)V _{REF} = 0V-30VVHigh-level input currentI _H V _{REF} = V _{DD} -11µAChw-level input currentI _H V _{REF} = 0V-30VLow-level input currentI _H V _{REF} = 0V-30µACrystal Oscillator Input (XIN)V _{REF} = 0V-30µACrystal Oscillator Input (XIN)V _{REF} = 0V-30µALow-level input currentI _H V _{REF} = 0V-30µACrystal Oscillator Output (XOUT)FxFundamental mode35MHZRecommended crystal load capacitance*C _{LDTAL} Fro best matching with internal crystal oscillator load16-18pFCrystal Oscillator Output (XOUT) </td <td></td> <td>l_i</td> <td>SDA, SCL in read condition</td> <td>-10</td> <td></td> <td>+10</td> <td>μA</td>		l _i	SDA, SCL in read condition	-10		+10	μA
High-level input voltage V_{H} $V_{DD} - 1.0$ V Low-level input current (pull-down) I_{H} $V_{ADDRx} = V_{DD}$ 30 μA Low-level input current (pull-down) I_{H} $V_{ADDRx} = 0V$ -1 1 μA Reference Frequency (Input (REF)-1 1 μA High-level input voltage V_{L} 0.8 V High-level input voltage V_{L} 0.8 V High-level input voltage V_{L} 0.8 V Low-level input current I_{H} $V_{REF} = V_{DD}$ -1 1 μA Sync Control Input (SNC) V_{L} 0.8 V High-level input voltage V_{L} $V_{DD} - 1.0$ V Low-level input current I_{H} $V_{REF} = 0V$ -30 μA Crystal Oscillator Input (SND) V_{L} $V_{DD} - 1.0$ V Crystal Oscillator Input Current I_{H} $V_{REF} = 0V$ -30 μA Crystal frequency F_X Fundamental mode 35 MHzCrystal frequency F_X Fundamental mode 40 μA Low-level input current I_{H} $V_{REF} = 0V; PCL mode-1010\mu ALow-level output $	Low-level output sink current (SDA)	I _{OL}	SDA in acknowledge condition; $V_{SDA} = 0.4V$	5	14		mA
Low-level input voltageVi0.8VHigh-level input current (pull-down)InVADDRx = VDD30µAReference Frequency Input (REF) </td <td>Address Select Input (ADDR0, ADDR1)</td> <td></td> <td></td> <td></td> <td></td> <td></td> <td></td>	Address Select Input (ADDR0, ADDR1)						
High-level input currentInitVADDRxVDD30 μ ALow-level input currentILVADDRx-11 μ AReference Frequency Input (REF)VDD-11 μ AHigh-level input voltageVILVDD0.8VLow-level input current (pull-down)ILVREF-11 μ ALow-level input current (pull-down)ILVREF0.8VSync Control Input (STRO)-30 μ AHigh-level input voltageVIL-30 μ ASync Control Input (STRO)VIL0.8VHigh-level input voltageVIL0.8VHigh-level input voltageVIL0.8VLow-level input voltageVIL0.8VLow-level input voltageVIL0.8VHigh-level input voltageVIL0.8VLow-level input currentILLVREF = VDD-11Low-level input currentILLVREF = 0V-30 μ ACrystal Scillator Input (XIN)TVDD-30 μ ACrystal Input currentILLVXIN = VDD-40	High-level input voltage	V _{IH}		$V_{DD} - 1.0$			V
Low-level input currentIn InV ADDRX BOD-11µAReference Frequency Input (REF)V InV V DoVV V V DoV V V V DoV V V V DoV V V V V DOV V V V V DOV V V V V V DOV V V V V V V V DO0.8V V V V V V A V N V N V N V Do0.8V V V V V V V V V V V V N V DO0.8V V V V V V V V V V V V V DO0.8V V V V V V V V V V V V DO0.8V V V V V V V V V V V DO0.8V V V V V V V V V V V DO0.8V V V V V V V V V V V DO0.8V V V V V V V V V V N Control Input (SYNC)V V V V V V V N Control Input (SYNC)V V V V V V V V N Control Input (V V V V N Control Input (V V N Control Input (V V V N Control Input (V N Control Input (V N V N Control Input (V N V N Control Input (V N Control Input (V N N Control Input (V N N Control Input (V N N Control Input (V N Control Input (V N Control Input (V N Control Input (V N N Control Input (V N N Control Input (V N N Control Input (V N N N Control Input (V N N N Con	Low-level input voltage	VIL				0.8	V
Reference Frequency Input (REF)nNormNormHigh-level input voltageViHViHVDD = 1.0VLow-level input voltageViL0.8VHigh-level input currentInput (SYNC)-11µALow-level input current (pull-down)InVREF = VDD-11µALow-level input current (pull-down)InVREF = 0V-30µALow-level input voltageViHVDD = 1.0VVDD = 1.0VLow-level input voltageViHVREF = VDD-11µALow-level input voltageViHVREF = 0V-30µALow-level input currentInitVREF = 0V-30µALow-level input current (pull-down)InVREF = 0V-30µALow-level input currentInitVREF = 0V-30µALow-level input currentInitVREF = 0D-11µALow-level input currentInitVREF = 0D-30µALow-level input currentInitVREF = 0D-30µA <t< td=""><td></td><td></td><td>$V_{ADDRx} = V_{DD}$</td><td></td><td>30</td><td></td><td>μA</td></t<>			$V_{ADDRx} = V_{DD}$		30		μA
High-level input voltage V_{H} $V_{DD} = 1.0$ V Low-level input voltage V_{IL} 0.8 V High-level input current I_{H} $V_{REF} = V_{DD}$ -11 μ ALow-level input current (pull-down) I_{IL} $V_{REF} = 0V$ -30 μ ASync Control Input (SYNC) $V_{DD} = 1.0$ V High-level input voltage V_{H} $V_{REF} = 0V$ 0.8 V Low-level input voltage V_{H} $V_{DD} = 1.0$ V V Low-level input voltage V_{H} $V_{REF} = 0V$ 0.8 V High-level input current I_{H} $V_{REF} = 0V$ $V_{DD} - 1.0$ V Low-level input current (pull-down) I_{L} $V_{REF} = 0V$ $V_{DD} - 1.0$ V Intreshold bias voltage V_{H} $V_{REF} = 0V$ $V_{DD} - 1.0$ V Intreshold bias voltage V_{H} $V_{REF} = 0V$ $V_{DD} - 1.0$ V Intreshold bias voltage V_{H} $V_{REF} = 0V$ $V_{DD} - 2.0V$ V High-level input current I_{H} $V_{XIN} = V_{DD}$ $V_{DD} - 2.0V$ V Recommended crystal load capacitance* $C_{L(RTAL)}$ For best matching with internal crystal f_{0-1} M Low-level output sink current I_{OH} $V_{OD} = 0.0V$ N Low-level output sink current <td></td> <td>IIL</td> <td>V_{ADDRx} = 0V</td> <td>-1</td> <td></td> <td>1</td> <td>μA</td>		IIL	V _{ADDRx} = 0V	-1		1	μA
Low-level input voltageV _L 0.8VHigh-level input currentI _H V _{REF} = V _{DD} -11µALow-level input current (pull-down)I _L V _{REF} = 0V-30µASync Control Input (SYNC)VV _{DD} - 1.0VLow-level input voltageV _H V _{DD} - 1.0VLow-level input currentI _H V _{REF} = V _{DD} -11µALow-level input currentI _H V _{REF} = V _{DD} -11µALow-level input currentI _H V _{REF} = 0V-30µACrystal Oscillator Input (XIN)TTTVThreshold bias voltageV _{TH} V _{DD} D40µACrystal Oscillator Input currentI _H V _{XIN} = V _{DD} 40µACrystal Oscillator Output (XOUT)FxFundamental mode35MHzRecommended crystal load capacitance*C _{L(XTAL} For best matching with internal crystal oscillator load16-18pFCrystal Oscillator Output (XOUT)IV _{XOUT} = 0-8.5mALow-level input currentIoLV _{XOUT} = 0-8.5mALow-level input sink currentIoLV _{XOUT} = 0-1010PECL Current Program I/O (IPRG)VVoc2.0V19mALow-level output sink currentIoLV _{OP} = 2.0V19mALow-level output sink currentIoLV _{OP} = 0.4V-35mAElock Outputs, CMOS Mode (CLKN, CLKP)V _{PRG} V _{PRG} or (V _{OD}	Reference Frequency Input (REF)						
High-level input currentI _H $V_{REF} = V_{DD}$ -11 μA Low-level input current (pull-down)I _L $V_{REF} = 0V$ -30 μA Sync Control Input (SYNC)	High-level input voltage			$V_{DD} - 1.0$			-
Low-level input current (pull-down)IL IL VREF = 0V-30ILA PASync Control Input (SYNC)VREF = 0V-30VSync Control Input (SYNC)VREF = VDD0.8VLow-level input voltageVILVREF = VDD-11Low-level input currentILVREF = VDD-11Low-level input currentILVREF = 0V-30VCrystal Oscillator Input (XIN)VREF = 0V-30VThreshold bias voltageVTHVREF = 0V-30VHigh-level input currentILVXIN = VDD-40VALow-level input currentILVXIN = ODD-40VACrystal Geallator Input (XIN)FxFundamental mode35MHzCrystal frequencyFxFundamental mode35MHzRecommended crystal load capacitance*CL(XTAL)Crystal reductor load16-18pFCrystal Oscillator Output (XOUT)VXOUT = 0-8.5MAPECL Current Program I/O (IPRG)VXOUT = VDD11MALow-level output source currentIDHVXOUT = 0-10IDLow-level output source currentIDHVog = 2.0V19mALow-level output sink currentIDHVog = 2.0V19mALow-level output sink currentIDHVog = 0.4V-35mALow-level output sink currentIDHVog = 0.4V-35mALow-level output sink currentIDHVog = 0.4V-35mA<	Low-level input voltage	VIL				0.8	V
Sync Control Input (SYNC)High-level input voltageV _{IL} V _{DD} - 1.0VLow-level input voltageV _{IL} 0.8VHigh-level input currentI _H V _{REF} = V _{DD} -11µALow-level input current (pull-down)I _{IL} V _{REF} = 0V-30µACrystal Oscillator Input (XIN)Treshold bias voltageV _{TH} V _{DD} /2VHigh-level input currentI _H V _{XIN} = V _{DD} 40µALow-level input currentI _{IL} V _{XIN} = GND-40µACrystal frequencyFxFundamental mode35MHzRecommended crystal load capacitance*C _{L(XTAL})For best matching with internal crystal oscillator load16-18pFCrystal Oscillator Output (XOUT)High-level output sink currentI _{OH} V _{XOUT} = 0-8.5mALow-level output source currentI _{OH} V _{XOUT} = 0-1010µAPECL Current Program I/O (IPRG)UV _{XOUT} = 0, -35mALow-level output source currentI _{OH} V _O = 2.0V19mAClock Outputs, PECL Mode (CLKN, CLKP)V _{IPRG} = 0V; PECL mode-1010µAHigh-level output sink currentI _{OL} V _O = 0.4V-35mALow-level output sink currentI _{OL} V _O = 0.4V-35mAElse soltageV _{IPRG} I _{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRGV _{DO} /3VIPRG bias currentI _{IPRG} I _{IPRG} </td <td></td> <td>l_{iH}</td> <td>$V_{REF} = V_{DD}$</td> <td>-1</td> <td></td> <td>1</td> <td>μA</td>		l _{iH}	$V_{REF} = V_{DD}$	-1		1	μA
High-level input voltageV _{IH} V _{DD} - 1.0VLow-level input voltageVIL0.8VIligh-level input currentIIHV _{REF} = V _{DD} -11µALow-level input current (pull-down)ILV _{REF} = 0V-30µACrystal Oscillator Input (XIN)TV-30µAChrystal Oscillator Input (XIN)VVVDD/2VThreshold bias voltageV _{TH} V _{XIN} = V _{DD} 40µALow-level input currentIIHV _{XIN} = GND40µACrystal frequencyFxFundamental mode35MHzRecommended crystal load capacitance*C _{L(XTAL)} For best matching with internal crystal16-18pFPigh-level output source currentIOHV _{XOUT} = 0-8.5mAMALow-level output source currentIOHV _{XOUT} = 0-1010µAPECL Current Program I/O (IPRG)IILV _{IPRG} = 0V; PECL mode-1010µAElock-Outputs, CMOS Mode (CLKN, CLKP)VO-35mAAPIRG bias voltageV _{IPRG} V _{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRGV _{DD} /3VIPRG bias currentI _{IPRG} I _{IPRG} or V _{IPRG} N/ING K _{IET} 3.5mA	Low-level input current (pull-down)	I _{IL}	V _{REF} = 0V		-30		μA
Low-level input voltage V_{IL} 0.8VHigh-level input current I_{H} $V_{REF} = V_{DD}$ -11 μ ALow-level input current I_{IL} $V_{REF} = 0V$ -30 μ ACrystal Oscillator Input (XIN)T $V_{DD}/2$ VThreshold bias voltage V_{TH} V_{DD} 40 μ ALow-level input current I_{IH} $V_{XIN} = V_{DD}$ -40 μ ACrystal frequency F_x Fundamental mode35MHzRecommended crystal load capacitance* $C_{L(XTAL)}$ For best matching with internal crystal oscillator load16-18pFCrystal Oscillator Output (XOUT)Itelevel input current I_{OH} $V_{XOUT} = 0$ -8.5mALow-level input current I_{OH} $V_{XOUT} = 0$ -8.5mALow-level input current I_{OH} $V_{VOUT} = 0$ -8.5mALow-level input current I_{OH} $V_{VOUT} = 0$ -8.5mALow-level input current I_{OH} $V_{VOUT} = 0$ -8.5mALow-level input current I_{OH} $V_{OP}G = 0.V$; PECL mode-1010 μ AClock Outputs, CMOS Mode (CLKN, CLKP)Item of the second of the seco	Sync Control Input (SYNC)						
High-level input currentI IHV NEEFV NEEF-11µALow-level input current (pull-down)ILV NEEFV-30µA Crystal Oscillator Input (XIN) TV DDV DD/2VHigh-level input currentIHV NLHV NLHV NLHV DD40µALow-level input currentIHV NLHV NLHV NLHV NLHV DD40µACrystal frequencyFxFundamental mode35MHzRecommended crystal load capacitance*C L(XTAL)For best matching with internal crystal oscillator load16-18PF Crystal Oscillator Output (XOUT) TN Nourt = 0-8.5mAHigh-level output source currentIOHV NOUT = V DD11mALow-level input currentIOHV NOUT = 0-1010µALow-level output source currentIOHV NOUT = VDD11mALow-level output source currentIOHV O = 2.0V19mALow-level output source currentIOHV O = 2.0V-35mAClock Outputs, CMOS Mode (CLKN, CLKP)V PEGL Mode (CLKN, CLKP)V PEGL Mode (CLKN, CLKP)N PEGL Mode (CLKN, CLKP)N PEGL Mode (CLKN, CLKP)N PEGL Mode (CLKN, CLKP)3.5MAIPRG bias voltageV PIPRGV PIPRG will be clamped to this level when a resistor is connected from VDD to IPRGN V DD/3V<	High-level input voltage	VIH		$V_{DD} - 1.0$			V
Low-level input current (pull-down)IL $V_{REF} = 0V$ -30 μA Crystal Oscillator Input (XIN)Threshold bias voltage V_{TH} $V_{DD}/2$ V Threshold bias voltage V_{TH} $V_{DD}/2$ V High-level input currentIL $V_{XIN} = V_{DD}$ 40 μA Low-level input currentIL $V_{XIN} = GND$ -40 μA Crystal frequency F_X Fundamental mode35MHzRecommended crystal load capacitance* $C_{L(XTAL)}$ For best matching with internal crystal oscillator load16-18 pF Crystal Oscillator Output (XOUT) $V_{XOUT} = 0$ -8.5mALow-level output sink currentIOH $V_{XOUT} = V_{DD}$ 11mAPECL Current Program I/O (IPRG) $V_{VOUT} = V_{DD}$ 10 μA Low-level output sink currentIOH $V_0 = 2.0V$ 19mALow-level output source currentIOH $V_0 = 2.0V$ 19mALow-level output source currentIOH $V_0 = 2.0V$ 3.5mALow-level output source currentIOH $V_0 = 0.4V$ -35mAClock Outputs, PECL Mode (CLKN, CLKP)IIIIIPRG bias voltage V_{IPRG} V_{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRG $V_{DD}/3$ V IPRG bias currentIpRG - (V_VDD - V_{IPRG}) / R_SET3.5mASink current to IPRG current ratioIIII	Low-level input voltage	VIL				0.8	V
Crystal Oscillator Input (XIN) V Threshold bias voltage V High-level input current I _{IH} V _{XIN} = V _{DD} 40 μ A Low-level input current I _{IL} V _{XIN} = GND -40 μ A Crystal frequency F _x Fundamental mode 35 MHz Recommended crystal load capacitance* C _{L(XTAL}) For best matching with internal crystal oscillator output (XOUT) 16-18 pF Crystal Oscillator Output (XOUT) For best matching with internal crystal oscillator output source current IOH V _{XOUT} = 0 -8.5 mA Low-level output source current IOH V _{XOUT} = 0 -8.5 mA Low-level output source current IOH V _{XOUT} = 0 -10 10 µA PECL Current Program I/O (IPRG) I V VIPRG = 0V; PECL mode -10 10 µA Low-level output source current IOH V _{IPRG} = 0V; PECL mode -10 10 µA Low-level output source current IOH V _{IPRG} = 0V; PECL mode -35 mA Low-level output source current IOH V _O = 2.0V 19 mA	High-level input current	I _{IH}		-1		1	μA
Threshold bias voltage V_{TH} $V_{DD}/2$ VHigh-level input current I_{IH} $V_{XIN} = V_{DD}$ 40 μA Low-level input current I_{L} $V_{XIN} = GND$ -40 μA Crystal frequency F_X Fundamental mode35MHzRecommended crystal load capacitance* $C_{L(XTAL)}$ For best matching with internal crystal oscillator load16-18pFCrystal Oscillator Output (XOUT)-8.5mAHigh-level output source current I_{OH} $V_{XOUT} = 0$ -8.5mALow-level output sink current I_{OL} $V_{XOUT} = V_{DD}$ 11mAPECL Current Program I/O (IPRG)-1010 μA Low-level output source current I_{OH} $V_{IPRG} = 0V$; PECL mode-1010 μA Clock Outputs, CMOS Mode (CLKN, CLKP)-35mA-35mALow-level output sink current I_{OH} $V_{0} = 2.0V$ 19mALow-level output sink current I_{OH} $V_{0} = 2.0V$ -35mALow-level output sink current I_{OL} $V_{0} = 0.4V$ -35mALow-level output sink current I_{OL} $V_{0} $	Low-level input current (pull-down)	IIL	V _{REF} = 0V		-30		μA
High-level input currentI _H $V_{XIN} = V_{DD}$ 40 μA Low-level input currentI _{IL} $V_{XIN} = GND$ -40 μA Crystal frequencyFxFundamental mode35MHzRecommended crystal load capacitance* $C_{L(XTAL)}$ For best matching with internal crystal oscillator load16-18pFCrystal Oscillator Output (XOUT)For best matching with internal crystal oscillator load16-18pFCrystal Oscillator Output source currentI _{OH} $V_{XOUT} = 0$ -8.5mALow-level output sink currentIoL $V_{XOUT} = V_{DD}$ 11mAPECL Current Program I/O (IPRG)IIViPRG = 0V; PECL mode-1010 μA Low-level output source currentI _{DH} $V_{o} = 2.0V$ 19mALow-level output source currentIOH $V_{O} = 2.0V$ -35mALow-level output source currentIOH $V_{O} = 0.4V$ -35mALow-level output source currentIOH $V_{O} = 0.4V$ -35mALow-level output source currentIOL $V_{O} = 0.4V$ -35mALow-level output source currentIOL V_{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRG $V_{DD}/3$ VIPRG bias currentI _{IPRG} I _{IPRG} – (V_VD – V_{IPRG}) / R_{SET}3.5mASink current to IPRG current ratioI _{IPRG} – (V_VD – V_{IPRG}) / R_{SET}3.5mA	Crystal Oscillator Input (XIN)						
Low-level input currentIIL $V_{XIN} = GND$ -40 μA Crystal frequency F_X Fundamental mode35MHzRecommended crystal load capacitance* $C_{L(XTAL)}$ For best matching with internal crystal oscillator load16-18pFCrystal Oscillator Output (XOUT)	Threshold bias voltage	V_{TH}			$V_{DD}/2$		V
Crystal frequency F_x Fundamental mode35MHzRecommended crystal load capacitance* $C_{L(XTAL)}$ For best matching with internal crystal oscillator load16-18pFCrystal Oscillator Output (XOUT)	High-level input current	I _{IH}	$V_{XIN} = V_{DD}$		40		μA
Recommended crystal load capacitance* $C_{L(XTAL)}$ For best matching with internal crystal oscillator load16-18pF Crystal Oscillator Output (XOUT) High-level output source current I_{OH} $V_{XOUT} = 0$ -8.5mALow-level output sink current I_{OL} $V_{XOUT} = V_{DD}$ 11mA PECL Current Program I/O (IPRG) Low-level input current I_{IL} $V_{IPRG} = 0V$; PECL mode-1010 μA Clock Outputs, CMOS Mode (CLKN, CLKP) High-level output sink current I_{OH} $V_0 = 2.0V$ 19mALow-level output sink current I_{OH} $V_0 = 2.0V$ 19mALow-level output sink current I_{OL} $V_0 = 0.4V$ -35mALow-level output sink current I_{OL} $V_0 = 0.4V$ -35mALow-level output sink current I_{OL} $V_0 = 0.4V$ -35mALow-level output sink current I_{OL} $V_{O} = 0.4V$ -35mALow-level output sink current I_{OL} $V_{DP/3}$ V IPRG bias voltage V_{IPRG} V_{IPRG} $V_{IPRG} - (V_{VDD} - V_{IPRG}) / R_{SET}$ 3.5mASink current to IPRG current ratio $I_{IPRG} - (V_{VDD} - V_{IPRG}) / R_{SET}$ 3.5mA	Low-level input current	IIL	V _{XIN} = GND		-40		μA
Recommended crystal load capacitance $O_{L(XTAL)}$ oscillator loadIB-16 pF Crystal Oscillator Output (XOUT)High-level output source current I_{OH} $V_{XOUT} = 0$ -8.5mALow-level output sink current I_{OL} $V_{XOUT} = V_{DD}$ 11mAPECL Current Program I/O (IPRG)Low-level input current I_{IL} $V_{IPRG} = 0V$; PECL mode-1010 μA Clock Outputs, CMOS Mode (CLKN, CLKP)High-level output source current I_{OH} $V_0 = 2.0V$ 19mALow-level output sink current I_{OL} $V_0 = 0.4V$ -35mALow-level output sink current I_{OL} $V_0 = 0.4V$ -35mALow-level output sink current I_{OL} $V_0 = 0.4V$ -35MALow-level output sink current I_{OL} V_{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRG $V_{DD}/3$ V IPRG bias current I_{IPRG} $I_{IPRG} - (V_{VDD} - V_{IPRG}) / R_{SET}$ 3.5mASink current to IPRG current ratio13131313	Crystal frequency	Fx	Fundamental mode			35	MHz
High-level output source currentI OHV XOUT = 0-8.5mALow-level output sink currentI I OLV XOUT = V DD11mAPECL Current Program I/O (IPRG)Low-level input currentI I I V V Nerdevel output source currentV I OHV V PECL mode-1010 V PAClock Outputs, CMOS Mode (CLKN, CLKP)V I Percevel output source currentI OHV O = 2.0V19mALow-level output sink currentI OL OLV O = 0.4V-35mAClock Outputs, PECL Mode (CLKN, CLKP)V IPRG bias voltageV IPRG will be clamped to this level when a resistor is connected from VDD to IPRGV VDD/3VIPRG bias currentI IPRGI IPRG - (VVDD - VIPRG) / RSET3.5mASink current to IPRG current ratioI 13II	Recommended crystal load capacitance*	$C_{\text{L}(\text{XTAL})}$	For best matching with internal crystal oscillator load		16-18		pF
Low-level output sink currentIoL $V_{XOUT} = V_{DD}$ 11mAPECL Current Program I/O (IPRG)Low-level input currentIIL $V_{IPRG} = 0V$; PECL mode-1010 μA Clock Outputs, CMOS Mode (CLKN, CLKP)High-level output source currentIOH $V_O = 2.0V$ 19mALow-level output sink currentIOL $V_O = 0.4V$ -35mAClock Outputs, PECL Mode (CLKN, CLKP)VIPRG will be clamped to this level when a resistor is connected from VDD to IPRG $V_{DD}/3$ VIPRG bias voltage V_{IPRG} $V_{IPRG} - (V_{VDD} - V_{IPRG}) / R_{SET}$ 3.5mASink current to IPRG current ratioIPRG - (V_VDD - V_{IPRG}) / R_SET1313	Crystal Oscillator Output (XOUT)						
PECL Current Program I/O (IPRG)Low-level input current I_{IL} V_{IPRG} = 0V; PECL mode-1010 μA Clock Outputs, CMOS Mode (CLKN, CLKP)High-level output source current I_{OH} V_0 = 2.0V19mALow-level output sink current I_{OL} V_0 = 0.4V-35mAClock Outputs, PECL Mode (CLKN, CLKP)VIPRG will be clamped to this level when a resistor is connected from VDD to IPRG $V_{DD}/3$ VIPRG bias voltage V_{IPRG} $I_{IPRG} - (V_{VDD} - V_{IPRG}) / R_{SET}$ 3.5mASink current to IPRG current ratio13131310	High-level output source current	I _{OH}					mA
PECL Current Program I/O (IPRG)Low-level input current I_{IL} $V_{IPRG} = 0V$; PECL mode-1010 μA Clock Outputs, CMOS Mode (CLKN, CLKP)High-level output source current I_{OH} $V_0 = 2.0V$ 19mALow-level output sink current I_{OL} $V_0 = 0.4V$ -35mAClock Outputs, PECL Mode (CLKN, CLKP) V_{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRG $V_{DD}/3$ VIPRG bias voltage V_{IPRG} $I_{IPRG} - (V_{VDD} - V_{IPRG}) / R_{SET}$ 3.5mASink current to IPRG current ratio $I_{IPRG} - (V_{VDD} - V_{IPRG}) / R_{SET}$ 1313	Low-level output sink current	IOL	$V_{XOUT} = V_{DD}$		11		mA
Clock Outputs, CMOS Mode (CLKN, CLKP) High-level output source current I _{OH} V _O = 2.0V 19 mA Low-level output sink current I _{OL} V _O = 0.4V -35 mA Clock Outputs, PECL Mode (CLKN, CLKP) VIPRG will be clamped to this level when a resistor is connected from VDD to IPRG V _{DD} /3 V IPRG bias voltage VIPRG IIPRG - (VVDD - VIPRG) / RSET 3.5 mA Sink current to IPRG current ratio IIPRG current ratio 13 13	PECL Current Program I/O (IPRG)						
High-level output source current I_{OH} $V_O = 2.0V$ 19mALow-level output sink current I_{OL} $V_O = 0.4V$ -35mAClock Outputs, PECL Mode (CLKN, CLKP) V_{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRG $V_{DD}/3$ V IPRG bias voltage V_{IPRG} $I_{IPRG} - (V_{VDD} - V_{IPRG}) / R_{SET}$ 3.5mASink current to IPRG current ratio131313			V _{IPRG} = 0V; PECL mode	-10		10	μA
High-level output source current I_{OH} $V_O = 2.0V$ 19mALow-level output sink current I_{OL} $V_O = 0.4V$ -35mAClock Outputs, PECL Mode (CLKN, CLKP) V_{IPRG} V_{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRG $V_{DD}/3$ V IPRG bias voltage V_{IPRG} $I_{IPRG} - (V_{VDD} - V_{IPRG}) / R_{SET}$ 3.5mASink current to IPRG current ratio131313	Clock Outputs, CMOS Mode (CLKN, CLK	<p)< td=""><td></td><td></td><td></td><td></td><td></td></p)<>					
Clock Outputs, PECL Mode (CLKN, CLKP) IPRG bias voltage V _{IPRG} V _{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRG V _{DD} /3 V IPRG bias current I _{IPRG} I _{IPRG} – (V _{VDD} – V _{IPRG}) / R _{SET} 3.5 mA Sink current to IPRG current ratio 13 13			$V_0 = 2.0V$		19		mA
Clock Outputs, PECL Mode (CLKN, CLKP) IPRG bias voltage V _{IPRG} V _{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRG V _{DD} /3 V IPRG bias current I _{IPRG} I _{IPRG} - (V _{VDD} - V _{IPRG}) / R _{SET} 3.5 mA Sink current to IPRG current ratio 13 13			$V_{\rm O} = 0.4 V$		-35		mA
IPRG bias voltage V _{IPRG} V _{IPRG} will be clamped to this level when a resistor is connected from VDD to IPRG V _{DD} /3 V IPRG bias current I _{IPRG} I _{IPRG} - (V _{VDD} - V _{IPRG}) / R _{SET} 3.5 mA Sink current to IPRG current ratio 13 13	Clock Outputs, PECL Mode (CLKN, CLK						
Sink current to IPRG current ratio 13					V _{DD} /3		V
Sink current to IPRG current ratio 13	IPRG bias current	I _{IPRG}	I _{IPRG} – (V _{VDD} – V _{IPRG}) / R _{SET}			3.5	mA
Tristate output current I ₂ -10 10 uA					13		
		17		-10		10	uА

Unless otherwise stated, VDD = $3.3V \pm 10\%$, no load on any output, and ambient temperature range $T_A = 0^{\circ}C$ to $70^{\circ}C$. Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits. MIN and MAX characterization data are $\pm 3\sigma$ from typical. Negative currents indicate flows out of the device.

Table 13: AC Timing Specifications

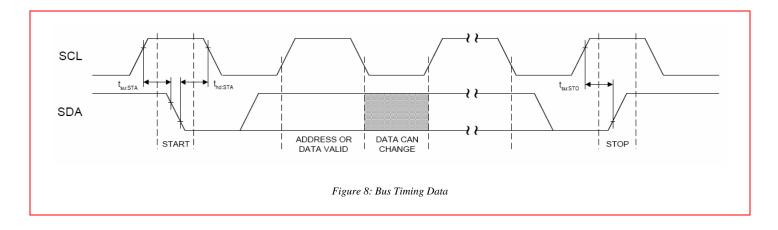
Parameter	Symbol	Conditions/Description	Clock (MHz)	Min.	Тур.	Max.	Units
Overall							
Output frequency*	$f_{o(max)}$	CMOS outputs PECL outputs		0 0		150 300	MHz
VCO frequency*	f _{vco}			40		400	MHz
CMOS mode rise time*	tr	C _L = 7pF			1		ns
CMOS mode fall time*	t _f	$C_L = 7pF$			1		ns
PECL mode rise time*	tr	$C_{L} = 7pF; R_{L} = 65 \text{ ohm}$			1		ns
PECL mode fall time*	t _f	$C_{L} = 7pF; R_{L} = 65 \text{ ohm}$			1		ns
Reference Frequency Inpu							
Input frequency	F _{REF}					80	MHz
Reference high time	t _{REHF}			3			ns
Reference low time	t _{REFL}			3			ns
Sync Control Input (SYNC	;)						
Sync high time	t _{SYNCH}	For orderly CLK stop/start		3			T _{CLK}
Sync low time	t _{SYNCL}	For orderly CLK stop/start		3			T _{CLK}
Clock Output (CLKP, CLK	(N)						
Duty cycle (CMOS mode)*		Measured at 1.4V			50		%
Duty cycle (PECL mode)*		Measured at zero crossings of ($V_{CLKP} - V_{CLKN}$)			50		%
		For valid programming solutions. Long-term (c position error of any edge compared with an i reference frequency. It is measured with a microsecond window, using statistics gathered o	deal clock time interv	génerateo al analyz	d from th	e same	ps
		FREF/NREF > 1000kHz			25		ps
Jitter, long term $(\sigma_y(\tau))^*$	t _{j(LT)}	FREF/NREF ~= 500kHz			50		ps
		FREF/NREF ~= 250kHz			100		ps
		FREF/NREF ~= 125kHz			190		ps
		FREF/NREF ~= 62.5kHz			240		ps
		FREF/NREF ~= 31.5kHz			300		ps
litter period (peak peak)*	+	40MHz < VCO frequency <100MHz			75		ps
Jitter, period (peak-peak)* $t_{j(\Delta P)}$		VCO frequency > 100MHz			50		ps

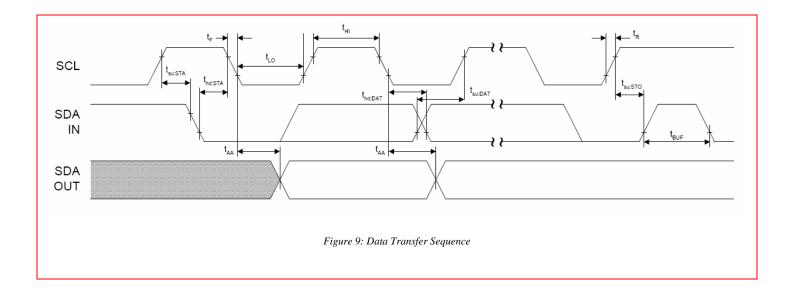
Unless otherwise stated, V_{DD} = 3.3V ± 10%, no load on any output, and ambient temperature range T_A = 0°C to 70°C. Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits. MIN and MAX characterization data are ± 3 σ from typical.

Table 14: Serial Interface Timing Specifications

Parameter	Symbol	Symbol Conditions/Description		Mode	Units	
			Min.	Max.		
Clock frequency	f _{SCL}	SCL	0	400	kHz	
Bus free time between STOP and START	t _{BUF}		1300		ns	
Set-up time, START (repeated)	T _{su:STA}		600		ns	
Hold time, START	t _{hd:STA}		600		ns	
Set-up time, data input	T _{su:DAT}	SDA	100		ns	
Hold time, data input	t _{hd:DAT}	SDA	0		ns	
Output data valid from clock	t _{AA}			900	ns	
Rise time, data and clock	t _R	SDA, SCL		300	ns	
Fall time, data and clock	t⊨	SDA, SCL		300	ns	
High time, clock	t _{HI}	SCL	600		ns	
Low time, clock	t _{LO}	SCL	1300		ns	
Set-up time, STOP	T _{su:STO}		600		ns	

Unless otherwise stated, V_{DD} = 3.3V ± 10%, no load on any output, and ambient temperature range T_A = 0°C to 70°C. Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits. MIN and MAX characterization data are ± 3 σ from typical.





8.0 Package Information for 'Green' and 'Non-Green'

Table 15: 16-pin SOIC (0.150") Package Dimensions

	Dimensions					
	Inc	hes	Millin	neters		
	Min.	Max.	Min.	Max.		
А	0.061	0.068	1.55	1.73		
A1	0.004	0.0098	0.102	0.249		
A2	0.055	0.061	1.40	1.55		
В	0.013	0.019	0.33	0.49		
С	0.0075	0.0098	0.191	0.249		
D	0.386	0.393	9.80	9.98		
Е	0.150	0.157	3.81	3.99		
е	0.050	BSC	1.27	BSC		
Н	0.230	0.244	5.84	6.20		
h	0.010	0.016	0.25	0.41		
L	0.016	0.035	0.41	0.89		
Θ	0°	8°	0°	8°		

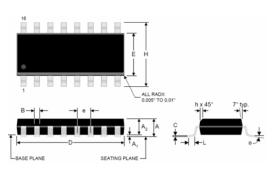


Table 16: 16-pin SOIC (0.150") Package Characteristics

Parameter	Symbol_	Conditions/Description	Тур.	Units
Thermal impedance, junction to free-air	Θ_{JA}	Air flow = 0ft./min.	108	°C/W
Lead inductance, self	1	Corner lead	2.5	nH
Leau inductance, sen	L11	Center lead	1.2	nH

Table 17: 16-pin 5.3mm (0.209") SSOP Package Dimensions

	Dimensions			
	Inc	Inches		neters
	Min.	Max.	Min.	Max.
А	0.068	0.078	1.73	1.99
A1	0.002	0.008	0.05	0.21
A2	0.066	0.070	1.68	1.78
В	0.010	0.015	0.25	0.38
С	0.005	0.008	0.13	0.20
D	0.239	0.249	6.07	6.33
Е	0.205	0.212	5.20	5.38
е	0.025	0.0256 BSC		BSC
Н	0.301	0.311	7.65	7.90
L	0.022	0.037	0.55	0.95
Θ	0	8	0	8

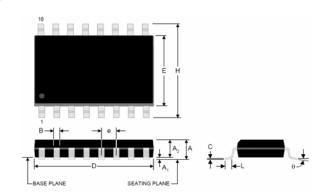


Table 18: 16-pin 5.3mm (0.208") SSOP Package Characteristics

Parameter	Symbol	Conditions/Description	Тур.	Units
Thermal impedance, junction to free-air	Θ_{JA}	Air flows = 0ft./min	90	°C/W
Lead inductance, self	L ₁₁	Corner lead	2.3	nH
Leau inductance, sen		Center lead	1	nH

9.0 Ordering Information

Part Number	Package	Shipping Configuration	Temperature Range
FS7145-01-XTD	16-pin (0.150") SOIC	Tube/Tray	0°C to 70°C (commercial)
FS7145-01-XTP	16-pin (0.150") SOIC	Tape & Reel	0°C to 70°C (commercial)
FS7140-02G-XTD	16-pin (5.3mm) SSOP 'Green' or lead-free packaging	Tube/Tray	0°C to 70°C (commercial)
FS7140-02G-XTP	16-pin (5.3mm) SSOP 'Green' or lead-free packaging	Tape & Reel	0°C to 70°C (commercial)
FS7140-01G-XTD	16-pin (0.150") SOIC 'Green' or lead-free packaging	Tube/Tray	0°C to 70°C (commercial)
FS7140-01G-XTP	16-pin (0.150") SOIC 'Green' or lead-free packaging	Tape & Reel	0°C to 70°C (commercial)

10.0 Revision History

Revision	Date	Modification
3	February 2006	
4	December 2007	Update to new AMIS template; update ordering codes
5	May 2008	Update to new ON Semiconductor template

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